

L Number	Hits	Search Text	DB	Time stamp
1	2	("4967256").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 11:03
7	170	semiconductor and (surge adj protector)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 11:42
13	300	emitter and base and buried and (surge overvoltage)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 13:20
19	3	(emitter and base and buried and (surge overvoltage)) and (semiconductor and (surge adj protector))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 12:22
25	2	("5001537").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 12:32
31	1	("5479031").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 12:32
37	12	emitter and base and buried and (surge overvoltage) and moat and ( oxide dielectric)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 14:03
43	12	(moat emitter) and base and buried and (surge overvoltage) and moat and ( oxide dielectric)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 14:07
49	0	((moat adj emitter) ( trench adj emitter)) and base and buried and (surge overvoltage) and moat and ( oxide dielectric)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 14:43
55	1	((moat adj emitter) ( trench adj emitter)) and base and buried and moat and ( oxide dielectric)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 14:59
61	168	((moat adj&? emitter) ( trench adj emitter)) and base and buried and moat and ( oxide dielectric)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 15:31
67	1	((moat adj emitter) ( trench adj emitter)) and base and buried and moat and ( oxide dielectric)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 15:46
73	2	((moat adj emitter) ( trench adj emitter))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 15:51
79	2	emitter near moat	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 16:12
85	89	emitter and moat and (diffusion implant) and oxide and filled	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/11 16:15